

Amendments to the Specification

Kindly amend paragraph [0017] as follows:

FIG. 2 shows another method to structure closely adjacent electrodes 202 on a substrate 104. In this method, a metal vapor 108, preferably Chromium or Gold, is deposited. Photo lacquer 102 is then deposited onto this metal layer 108, and is structured according to the components to be produced. For example, as shown in FIG. 2, a portion of the surface of metal layer 108 does not have photo lacquer 102 thereon. In the subsequent method step, the metal 108 is etched at all points 204 not covered by the photo lacquer 102, whereby the metal 108 is ~~over-cut~~ undercut at the edges of the photo lacquer 102 in a controlled manner.

Kindly amend paragraph [0018] as follows:

Overhangs 206 thus are formed on each photo lacquer 102. Subsequently, the structure thus achieved again receives a deposit of metal vapor 208. For example, as shown in FIG. 2, a surface of photo lacquer 102 and an exposed portion of substrate 104 where metal layer 108 was etched away are exposed to the deposit of metal vapor 208 so that second metal layer 208 is formed on the surface of photo lacquer 102 and the exposed portion of substrate 104 where the metal layer 108 was etched away, except in a space between overhang 206 and substrate 104. The electrodes 202 are separated from each other by means of the undercutting. After the photo lacquer 102 is removed (lift off) with its deposited metal layer 208, the desired electronic component (field-effect transistor) 116 may be completed using known method steps by scattering an organic semi-conductor ('active layer') 118 and

an insulator 110, or deposition of gate metallization 302 and exposure-etching 304 of the connectors (FIG. 3). To the extent the deeper-positioned electrodes are to be formed, for example, the gates of a transistor, they are purposefully so covered with an insulator that the recess is also closed by means of it.

Kindly amend paragraph [0021] as follows:

Another method to produce electronic components with closely adjacent electrodes 202 on a substrate 104 is shown in FIGS. 2 and 5 for the example of the production of a field-effect transistor 116. The structuring of these closely adjacent electrodes 202 is performed as in the above-described method (Method 2). Holes or grooves 502 for one or more gates buried are etched into those positions of the substrate 104 at which no metal layer 108 is present. For example, as shown in FIG. 5, a hole 502 is etched into substrate 104 at a position other than a position of metal layer 108 and second metal layer 208 (from FIG. 2). In the subsequent method step, a ~~second~~ third vapor-metal layer 504 is deposited to the entire surface. For example, as shown in FIG. 5, third metal layer 504 is deposited onto substrate 104, metal layer 108, and second metal layer 208 (from FIG. 2). Thin gate metallizations are deposited in the holes or grooves 502. An insulator 110 is subsequently deposited on the surface thus produced. For example, as shown in FIG. 5, insulator 110 is applied to third metal layer 504. The holes or grooves 502 are partially filled by the insulator 110. The insulation 110 is etched away on the upper side of the substrate 104 using, for example, a plasma process, and is only partially etched away in the holes or grooves 502 because of the aspect ratios. For example, as shown in FIG. 5, a portion of insulator 110 at the position of metal layer 108 and second metal layer 208 (from FIG. 2) is etched. The organic

semiconductor ('active layer') 118 is subsequently applied. For example, as shown in FIG. 5, organic semiconductor 118 is applied to third metal layer 504 and insulator 110. After the surface of the substrate 104 is sealed 506, the contacts of the buried gates must be exposed by means of a photolithographic process. For example, as shown in FIG. 5, sealing layer 506 is applied to organic semiconductor 118.